

T-43-21



## CMOS Strobed Hex Inverter/Buffer

### High-Voltage Types (20-Volt Rating)

CD4502B consists of six inverter/buffers with 3-state outputs. A logic "1" on the OUTPUT DISABLE input produces a high-impedance state in all six outputs. This feature permits common busing of the outputs, thus simplifying system design. A Logic "1" on the INHIBIT input switches all six outputs to logic "0" if the OUTPUT DISABLE input is a logic "0". This device is capable of driving two standard TTL loads, which is equivalent to six times the JEDEC "B" series  $I_{OL}$  standard.

The CD4502B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic package (E suffix), and in chip form (H suffix). This device is similar to the MC14502.

#### MAXIMUM RATINGS, Absolute-Maximum Values:

##### DC SUPPLY-VOLTAGE RANGE, ( $V_{DD}$ )

Voltages referenced to  $V_{SS}$  Terminal ..... -0.5V to +20V

##### INPUT VOLTAGE RANGE, ALL INPUTS

..... -0.5V to  $V_{DD}$  +0.5V

##### DC INPUT CURRENT, ANY ONE INPUT

.....  $\pm 10\text{mA}$

##### POWER DISSIPATION PER PACKAGE (PD):

For  $T_A = -55^\circ\text{C}$  to  $+100^\circ\text{C}$  ..... 500mW

For  $T_A = +100^\circ\text{C}$  to  $+125^\circ\text{C}$  ..... Derate Linearly at 12mW/ $^\circ\text{C}$  to 200mW

##### DEVICE DISSIPATION PER OUTPUT TRANSISTOR

FOR  $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (All Package Types)}$  ..... 100mW

OPERATING-TEMPERATURE RANGE ( $T_A$ ) ..... -55 $^\circ\text{C}$  to +125 $^\circ\text{C}$

STORAGE TEMPERATURE RANGE ( $T_{STG}$ ) ..... -65 $^\circ\text{C}$  to +150 $^\circ\text{C}$

##### LEAD TEMPERATURE (DURING SOLDERING):

At distance  $1/16 \pm 1/32$  inch ( $1.59 \pm 0.79$  mm) from case for 10s max ..... +285 $^\circ\text{C}$

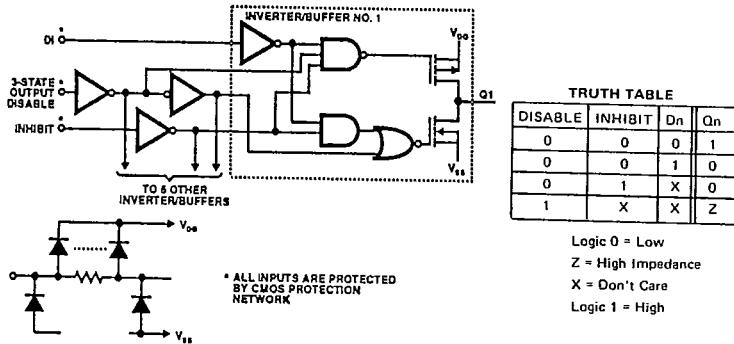
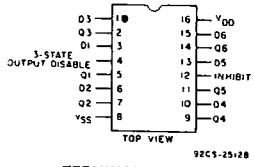


Fig. 1 - Logic diagram of 1 of 6 identical inverter/buffers.



TERMINAL ASSIGNMENT

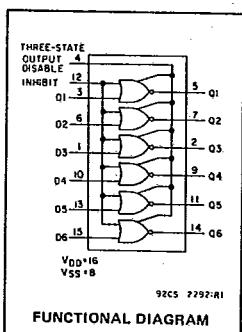
#### Features:

- 2 TTL-load output drive capability
- 3-state outputs
- Common output-disable control
- Inhibit control
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Maximum input current of 1  $\mu\text{A}$  at 18 V over full package-temperature range; 100 nA at 18 V and 25 $^\circ\text{C}$
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"
- Noise margin (full package-temperature range) =

$$\begin{aligned} 1 \text{ V at } V_{DD} &= 5 \text{ V} \\ 2 \text{ V at } V_{DD} &= 10 \text{ V} \\ 2.5 \text{ V at } V_{DD} &= 15 \text{ V} \end{aligned}$$

#### Applications:

- 3-state hex inverter for interfacing IC's with data buses
- COS/MOS to TTL hex buffer



FUNCTIONAL DIAGRAM

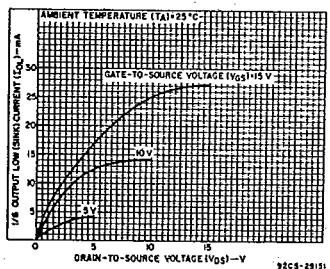


Fig. 2 - Typical output low (sink) current characteristics.

**COMMERCIAL CMOS  
HIGH VOLTAGE IC'S**

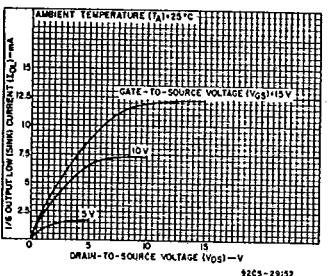


Fig. 3 - Minimum output low (sink) current characteristics.

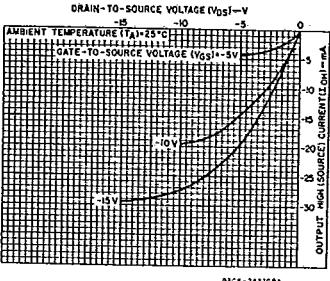


Fig. 4 - Typical output high (source) current characteristics.

## CD4502B Types

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## RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
Supply-Voltage Range (For $T_A =$ Full Package-Temperature Range)	3	18	V

## STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES ( $^{\circ}\text{C}$ )						UNITS	
	$V_O$ (V)	$V_{IN}$ (V)	$V_{DD}$ (V)	-55	-40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, $I_{DD}$ Max	-	0.5	5	1	1	30	30	-	0.02	1	$\mu\text{A}$
	-	0.10	10	2	2	60	60	-	0.02	2	
	-	0.15	15	4	4	120	120	-	0.02	4	
	-	0.20	20	20	20	600	600	-	0.04	20	
Output Low (Sink) Current, $I_{OL}$ Min	0.4	0.5	5	3.84	3.66	2.52	2.16	3.06	6	-	$\text{mA}$
	0.5	0.10	10	9.6	9	6.6	5.4	7.8	15.6	-	
	1.5	0.15	15	25.2	24	16.8	14.4	20.4	40.8	-	
Output High (Source) Current, $I_{OH}$ Min	4.6	0.5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	$\text{mA}$
	2.5	0.5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-	
	9.5	0.10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	
	13.5	0.15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-	
Output Voltage Low-Level, $V_{OL}$ Max	-	0.5	5	0.05			-	0	0.05	$\text{V}$	
	-	0.10	10	0.05			-	0	0.05		
	-	0.15	15	0.05			-	0	0.05		
Output Voltage High Level, $V_{OH}$ Min	-	0.5	5	4.95			4.95	5	-	$\text{V}$	
	-	0.10	10	9.95			9.95	10	-		
	-	0.15	15	14.95			14.95	15	-		
Input Low Voltage, $V_{IL}$ Max	0.5, 4.5	-	5	1.5			-	-	1.5	$\text{V}$	
	1.9	-	10	3			-	-	3		
	15, 13.5	-	15	4			-	-	4		
Input High Voltage, $V_{IH}$ Min	4.5	-	5	3.5			3.5	-	-	$\text{V}$	
	9	-	10	7			7	-	-		
	13.5	-	15	11			11	-	-		
Input Current, $I_{IN}$ Max		0.18	18	$\pm 0.1$	$\pm 0.1$	$\pm 1$	$\pm 1$	-	$\pm 10^{-5}$	$\pm 0.1$	$\mu\text{A}$
3-State Output Leakage Current, $I_{OUT}$ Max	0.18	0.18	18	$\pm 0.4$	$\pm 0.4$	$\pm 12$	$\pm 12$	-	$\pm 10^{-4}$	$\pm 0.4$	$\mu\text{A}$

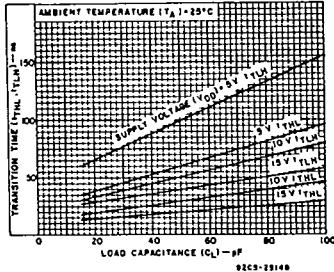


Fig.8 - Typical transition time as a function of load capacitance.

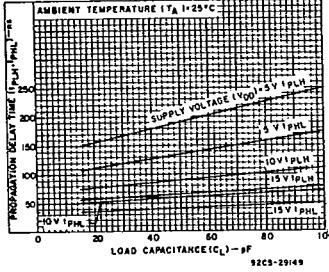


Fig.9 - Typical propagation-delay time as a function of load capacitance.

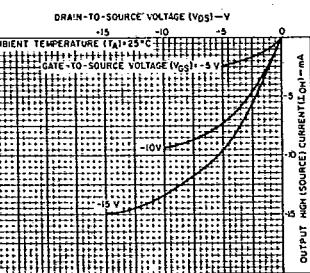


Fig.5 - Minimum output high (source) current characteristics.

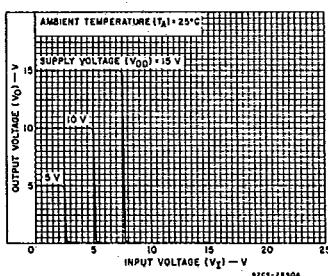


Fig.6 - Typical voltage transfer characteristic.

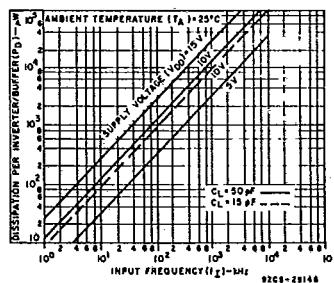


Fig.7 - Typical power dissipation as a function of input frequency.

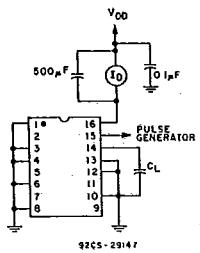


Fig.10 - Power-dissipation test circuit.

## CD4502B Types

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DYNAMIC ELECTRICAL CHARACTERISTICS at  $T_A = 25^\circ\text{C}$ ; Input  $t_r, t_f = 20 \text{ ns}$ ,  
 $C_L = 50 \text{ pF}, R_L = 200 \text{ k}\Omega$  Unless otherwise specified.

CHARACTERISTIC	TEST CONDITIONS	LIMITS		UNITS
		V <sub>DD</sub> (V)	TYP	
Data or Inhibit Delay Times:	High to Low, t <sub>PHL</sub>	5	135	270
		10	60	120
		15	40	80
	Low to High, t <sub>PLH</sub>	5	190	380
		10	90	180
		15	65	130
Disable Delay Times: R <sub>L</sub> =1 k $\Omega$	Output High to High Impedance, t <sub>PHZ</sub>	5	60	120
		10	40	80
		15	30	60
	High Impedance to Output High, t <sub>PZH</sub>	5	110	220
		10	50	100
		15	40	80
Output Low to High Impedance, t <sub>PLZ</sub>	See Fig. 14	5	125	250
		10	65	130
		15	55	110
	High Impedance to Output Low, t <sub>ZPL</sub>	5	125	250
		10	55	110
		15	40	80
Transition Times:	Low to High, t <sub>TLH</sub>	5	100	200
		10	50	100
		15	40	80
	High to Low, t <sub>THL</sub>	5	60	120
		10	30	60
		15	20	40
Input Capacitance, C <sub>IN</sub>	Any Input	5	7.5	pF
Output Capacitance, C <sub>OUT</sub>		7-8	15	pF

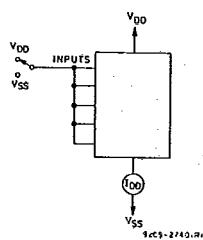


Fig. 11 — Quiescent-device-current test circuit.

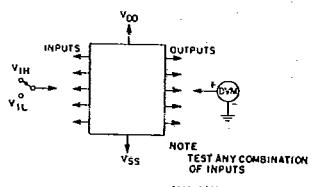


Fig. 12 — Input-voltage test circuit.

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HIGH VOLTAGE ICs**

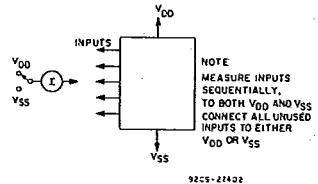


Fig. 13 — Input leakage current test circuit.

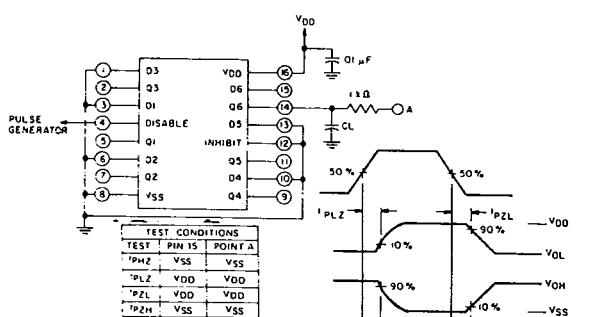
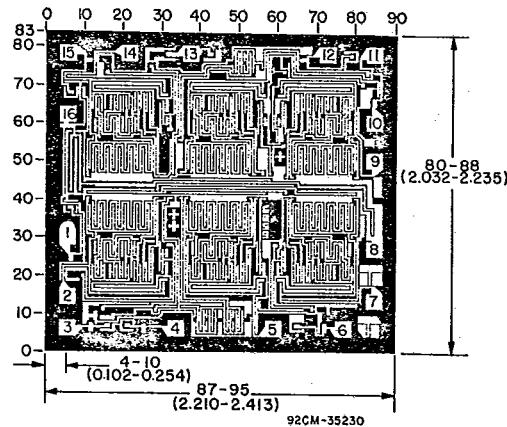


Fig. 14 — Disable delay times test circuit and waveforms.



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils ( $10^{-3}$  inch).